

# JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

# **TO-92 Plastic-Encapsulate Thyristors**

# MAC97A6,A8 TRIAC

### **MAIN FEATURES**

Sym	value	unit	
I <sub>T(R</sub>	1	Α	
$V_{DRM}/V_{RRM}$	MAC97A6	400	V
	MAC97A8	600	V
I <sub>TS</sub>	8	Α	

# TO-92 1. ANODE 2. GATE 3. ANODE 123 T20 T10 G

### **DESCRIPTION**

Logic level sensitive gate triac intended to be interfaced directly to microcontrollers, logic integrated circuits and other low power gate trigger circuits.

### **FEATURES**

- Blocking voltage to 400 V (MAC97A6)
- RMS on-state current to 0.6 A
- General purpose bidirectional switching

### **APPLICATIONS**

- General purpose bidirectional switching
- Phase control applications
- Solid state relays

# **Limiting values**

Symbol	Parameter	Conditions	Value	Unit	
V <sub>DRM</sub> /V <sub>RRM</sub>	I TEDELLIVE DEAK UIT-SLALE VUILAUE IVIAUSTAL	T <sub>j</sub> = 25 to125 ℃	400	V	
	MAC97A8	T <sub>j</sub> = 25 to125 <b>℃</b>	600		
I <sub>GM</sub>	gate current(peak value)	t = 2µs max	1	Α	
$V_{GM}$	gate voltage(peak value)	t = 2µs max	5	V	
P <sub>GM</sub>	gate power(peak value)	t = 2µs max	5	W	
<b>T</b> j	Junction Temperature	-	-40 ~ 125	$^{\circ}$	
T <sub>stq</sub>	Storage Temperature	_	-40 ~ 150	$^{\circ}$	

# ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

Parameter		Symbol	Test conditions		Min	Max	Unit
Rated repetitive peak off-state/reverse voltage		$V_{DRM,}V_{RRM}$	I <sub>D</sub> =10μA	MAC97A6 MAC97A8	400 600		V
Rated repetitive peak off-state current		I <sub>DRM</sub>	V <sub>D</sub> =V <sub>DRM</sub>		000	10	μA
On-state voltage		V <sub>TM</sub>	I <sub>T</sub> =1A,I <sub>G</sub> =50mA			1.9	V
	I	- I <sub>GT</sub>	T <sub>2</sub> (+), G(+)			5	mA
Gate trigger current	II		T <sub>2</sub> (+), G(-)	V <sub>D</sub> =12V		5	mA
Gate trigger current	Ш		T <sub>2</sub> (-), G(-)	R <sub>L</sub> =100Ω		5	mA
	IV		T <sub>2</sub> (-), G(+)			ı	mA
	I		T <sub>2</sub> (+), G(+)			1.5	<b>V</b>
Gate trigger voltage	II	V <sub>GT</sub>	T <sub>2</sub> (+), G(-)	V <sub>D</sub> =12V		1.5	<b>&gt;</b>
Gate trigger voltage	Ш		T <sub>2</sub> (-), G(-)	R <sub>L</sub> =100Ω		1.5	V
	IV		T <sub>2</sub> (-), G(+)			-	V
Holding current		I <sub>H</sub>	I <sub>T</sub> =600mA ,I <sub>G</sub> =20mA			10	mA